

## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

Claims 1-15 (Canceled)

Claim 16 (Original) A method of manufacturing semiconductor light-emitting device comprising the steps of:

growing a compound semiconductor epitaxial layer including an active layer on a substrate having a surface having an off-angle to a crystallographic plane of low-degree surface orientation;

forming a protective film having an opening on a surface of the compound semiconductor epitaxial layer; and

selectively growing a ridge-shaped compound semiconductor epitaxial layer to cover the opening.

Claim 17 (Original) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the compound semiconductor epitaxial layers including an active layer further include a first conductivity type cladding layer and a second conductivity type first cladding layer.

Claim 18 (Original) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the ridge-shaped compound semiconductor epitaxial layer includes a second conductivity type second cladding layer.

Claim 19 (Original) The method for manufacturing semiconductor light-emitting device according to claim 18, wherein the second conductivity type second cladding layer is grown as to cover a portion of a surface of the protective film.